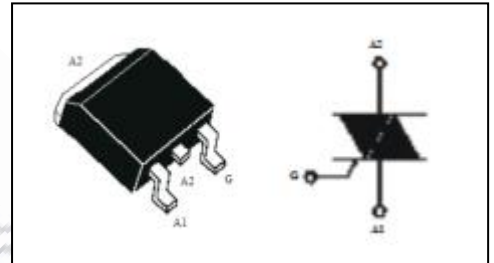


isc Thyristors
T2535-800G
APPLICATIONS

- With TO-263 package.
- Be suitable for general purpose AC switching, they can be used as an ON/OFF function in applications.
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.


ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V _{DRM}	Repetitive peak off-state voltage	600	V
V _{RRM}	Repetitive peak reverse voltage	800	V
I _{T(RMS)}	RMS on-state current @T _c =100°C	25	A
I _{TSM}	Surge non-repetitive on-state current F=50HZ; t=20ms F=60HZ; 16.7ms	250 260	A
P _{G(AV)}	Average gate power dissipation @T _j =100°C	1	W
T _j	Operating junction temperature	-40~125	°C
T _{stg}	Storage temperature	-40~150	°C

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I _{RRM}	Repetitive peak reverse current	V _{RM} =V _{RRM}	T _j =25°C	5	μA
			T _j =125°C	3	mA
I _{DRM}	Repetitive peak off-state current	V _{DM} =V _{DRM}	T _j =25°C	5	μA
			T _j =125°C	3	mA
V _{TM}	On-state voltage	I _{TM} = 35A; t _p =380 μs		1.75	V
I _{GT}	Gate-trigger current (minimum IGT is guaranteed at 5% of IGT max) Quadrant(I - II - III)	V _D = 12 V; R _L =30 Ω		35	mA
V _{GT}	Gate-trigger voltage Quadrant (I - II - III)	V _D = 12 V; R _L =30 Ω		1.3	V
R _{th(j-c)}	Thermal resistance	Junction to case		0.8	°C/W